Product data sheet

1. Product profile

1.1 General description

Single high-voltage switching diode, encapsulated in a SOD123F small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Small and flat lead SMD plastic package
- Reverse voltage: V_R ≤ 200 V

1.3 Applications

General-purpose switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		<u>[1]</u> -	-	200	mA
V_R	reverse voltage		-	-	200	V
t _{rr}	reverse recovery time		[2] -	-	50	ns

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

[2] When switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 $\Omega;$ measured at I_R = 3 mA.



Single high-voltage switching diode

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode	[1]	
2	anode	1 2	1 🕂 2
			sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BAS21H	-	plastic surface-mounted package; 2 leads	SOD123F

4. Marking

Table 4. Marking codes

Type number	Marking code
BAS21H	B2

Single high-voltage switching diode

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	250	V
V_R	reverse voltage		-	200	V
I _F	forward current		<u>[1]</u> -	200	mA
I _{FRM}	repetitive peak forward current	t_p = 1 ms; δ = 0.25	-	625	mA
I _{FSM}	non-repetitive peak forward current	square wave	[2]		
		t _p = 1 μs	-	9	Α
		t _p = 100 μs	-	3	Α
		$t_p = 10 \text{ ms}$	-	1.7	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[3] _	375	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	330	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[3] _	-	70	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] $T_i = 25$ °C prior to surge.

^[3] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint

^[2] Reflow soldering is the only recommended soldering method.

^[3] Soldering point of cathode tab.

Single high-voltage switching diode

7. Characteristics

Table 7. Characteristics

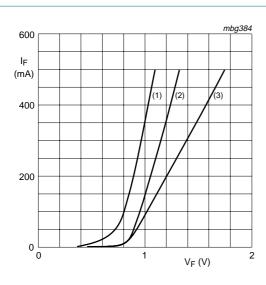
 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

ramb – 20	Tamb = 20 C unicos cinervice opecined.						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _F forward voltage	$I_F = 100 \text{ mA}$	[1]	-	-	1	V	
		$I_F = 200 \text{ mA}$	[1]	-	-	1.25	V
I _R reverse current	reverse current	V _R = 200 V		-	-	100	nA
	$V_R = 200 \text{ V}; T_j = 150 ^{\circ}\text{C}$		-	-	100	μΑ	
C_{d}	diode capacitance	$V_R = 0 V$; $f = 1 MHz$		-	-	5	pF
t _{rr}	reverse recovery time		[2]	-	-	50	ns

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

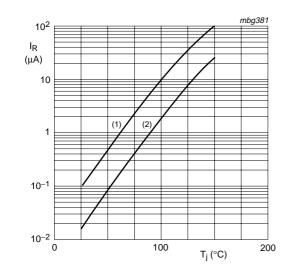
^[2] When switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω ; measured at I_R = 3 mA.

Single high-voltage switching diode



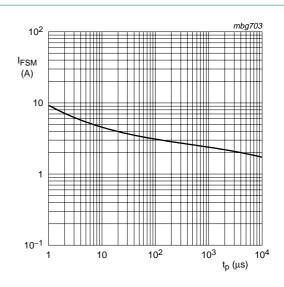
- (1) $T_{amb} = 150 \,^{\circ}C$; typical values
- (2) $T_{amb} = 25 \,^{\circ}C$; typical values
- (3) $T_{amb} = 25 \,^{\circ}C$; maximum values

Fig 1. Forward current as a function of forward voltage



- (1) $V_R = V_{Rmax}$; maximum values
- (2) $V_R = V_{Rmax}$; typical values

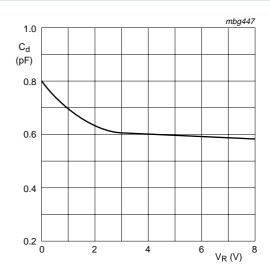
Fig 3. Reverse current as a function of junction temperature



Based on square wave currents.

T_i = 25 °C; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values

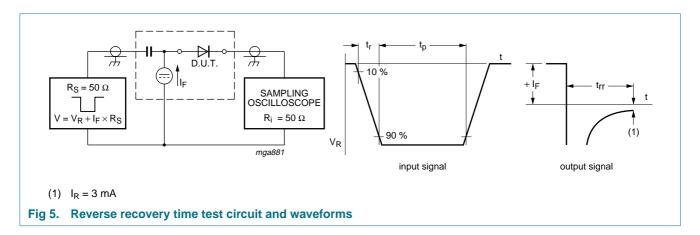


 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}$

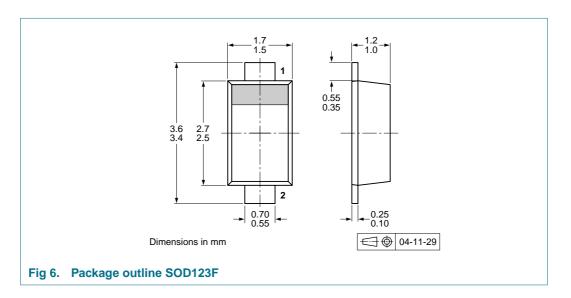
Fig 4. Diode capacitance as a function of reverse voltage; typical values

Single high-voltage switching diode

8. Test information



9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

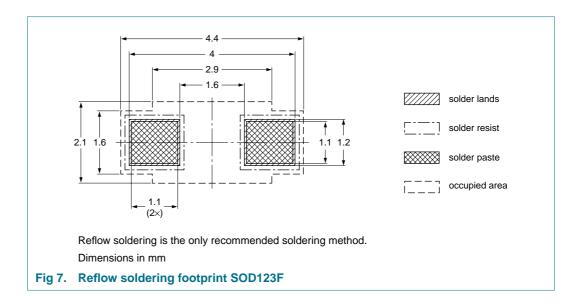
Type number	Package	Description	Packing quantity	
			3000	10000
BAS21H	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135

^[1] For further information and the availability of packing methods, see Section 15.

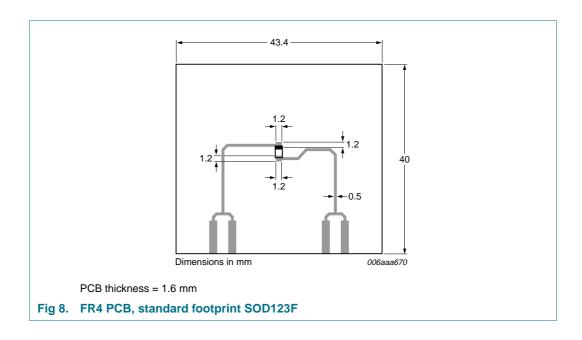
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11. Soldering



12. Mounting



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13. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BAS21H_2	20061103	Product data sheet	-	BAS21H_1			
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity			
	 Legal texts 	have been adapted to the n	ew company name whe	re appropriate.			
	• Section 1.1	"General description": ame	nded				
	Table 1 "Quick reference data": I _F forward current table note added						
	Table 5 "Limiting values": I _F forward current table note added						
	Table 5 "Limiting values": I _{FRM} repetitive peak forward current condition amended						
	Table 5 "Limiting values": I _{FSM} non-repetitive peak forward current condition amended						
	Table 6: R _{th(i-sp)} thermal resistance from junction to solder point table note added						
	Table 7 "Characteristics": V _F forward voltage unit amended						
	Figure 2: figure title and figure note amended						
	• Figure 3: an	nended					
	Section 12 "Mounting": added						
	Section 14.4	4 "Trademarks": added					
BAS21H_1	20050411	Product data sheet	-	-			

Single high-voltage switching diode

14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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